9th International Workshop on Characterization and Modeling of Memory devices

September 27th - 28th 2018

University of Milano-Bicocca, Building U6, Room U6-09 (Ground Floor)
Piazza dell'Ateneo Nuovo 1, Milan (Italy)

SCHEDULE

SEPTEMBER 27th

9.30 a.m. Registration

10.10 a.m. **Welcome**
Gianfranco **Pacchioni**, Pro-Rector for Research, University of Milano-Bicocca

10.20 a.m. 1st Session: Plenary Talks

10.20 a.m. *Integrating CMOS and emerging memories for machine learning* - Yusuf **Leblebici** - EPFL, Lausanne - Switzerland
11.05 a.m. *Spin-Transfer-Torque MRAM: the Next Revolution in Memory* - Daniel C. **Worledge** - IBM Almaden Research Center - USA
11.50 a.m. *Scaling Perspectives of 3D NAND* - Akira **Goda** - Micron Tecnhology, Boise - USA

12.35 a.m. **Lunch**

2.00 p.m. 2nd Session: Phase Change and Ovonic Materials

2.00 p.m. *Ab initio Guided Design of an Ultrafast Phase-Change Material* - Riccardo **Mazzarello** - Aachen University - Germany
2.35 p.m. *Exploiting Nanoscale Effects in Phase-Change Memories* - Martin **Salinga** - Aachen University - Germany
3.10 p.m. *Terahertz Studies in Phase Change Materials: Toward Ultrafast Phase Change Operation and Photonics* - Kotaro **Makino** - AIST, Tsukuba - Japan
3.45 p.m. *Ovonic Threshold Switching Selector and Non-Volatile Resistive Memory Co-Integration Towards 3D PCM and RRAM Crossbar Memory Featuring High Density and High Endurance Performance* - Gabriele **Navarro** - CEA, LETI, Grenoble - France

4.20 p.m. **Coffee Break**

SEPTEMBER 28th

9.00 a.m. 3rd Session: Oxide RRAM

9.00 a.m. *Cross-layer Design Strategy for Accelerating Deep Learning Using Emerging Resistive Memory Technology* - Tuo-Hung **Hou** - National Chiao Tung University - Taiwan
9.35 a.m. *Multiscale Modeling of Novel Memory Devices: Linking Materials to Devices for Accurate Performance and Reliability Predictions* - Luca **Larcher** - University of Modena and Reggio Emilia - Italy
10.10 a.m. *Oxide RRAM for Spiking Neural Networks* - Sabina **Spiga** - CNR-IMM, Agrate Brianza - Italy

10.45 a.m. **Coffee Break**

11.15 a.m. 4th Session: Ferroelectrics and Ferromagnetics

11.15 a.m. *A Potential Alternative for DRAM and NAND: Ferroelectric HfO2 Thin Film* - Karine **Florent** - KU Leuven - Belgium
11.50 a.m. *Current Status of FeRAM Technologies and Prospects for Beyond Memory Application* - Stefan **Slesazeck** - NaMLab, Dresden - Germany
12.25 a.m. *Towards High Density STT-MRAM at sub-20nm Nodes* - Bernard **Dieny** - Université Grenoble Alpes - France

1.00 p.m. **Lunch & Adjourn**

CLICK HERE TO REGISTER
More info available on the workshop website at **www.iwcm2.eu**

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